

7250 **COIL PRE-DRIVE** FOR BUBBLE MEMORIES

7250	0 to 70°C			
7250-5	-20 to +85°C			

- Very Low Power
- Power Fail Reset for Maximum **Protection of Bubble Memory**
- TTL Compatible Inputs

- Only One Power Supply Required, +12V
- **CMOS Technology**
- Standard 16-Pin Dual In-Line Package

The Intel 7250 is a low power Coil Pre-Driver (CPD) for use with Intel Magnetics Bubble Memories. The 7250 is controlled by the Intel 7220-1 Bubble Memory Controller (BMC) and directly drives Quad VMOS transistor packs, which are connected to the coils of the bubble memory.

The 7250 is a high-voltage, high-current driver constructed using CMOS technology. The device has TTL compatible inputs and the outputs are designed to drive either low on-resistance VMOS transistors or bipolar transistors.

The 7250 is in a standard 16-pin dual in-line package.

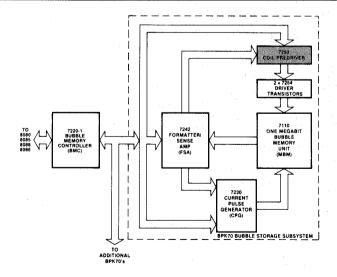




Figure 1. Block Diagram of Single Bubble Memory System-128K Bytes

Figure 2. Pin Configuration



Table 1. Pin Description

Symbol	Pin No.	Description					
ČŠ 1		Chip select. It is active low. When high chip is deselected and IDD is significantly reduced.					
RESET	2	Active low input from RESET.OUT of 7220-1 Controller forces 7250 outputs inactive so that bubble memory is protected in the event of power supply failure.					
$\overline{X} + \overline{IN}$, $.\overline{X}\overline{IN}$	3, 4	Active low inputs from Controller which turn on the high-current X outputs.					
XOUT XOUT X+.OUT X+.OUT	12, 13, 14, 15	High-current outputs and their complements for driving the gates of the 7254 VMOS quad transistors which in turn drive the X coils of the bubble memory.					
$\overline{Y}+.\overline{IN}, \overline{Y}\overline{IN}$	5, 6	Active low inputs from Controller which turn on the high-current Youtputs.					
Y-OUT YOUT Y+.OUT Y+.OUT	7, 9, 10, 11	High-current outputs and their complements for driving the gates of the 7254 VMOS quad transistors which in turn drive the Y coils of the bubble memory.					

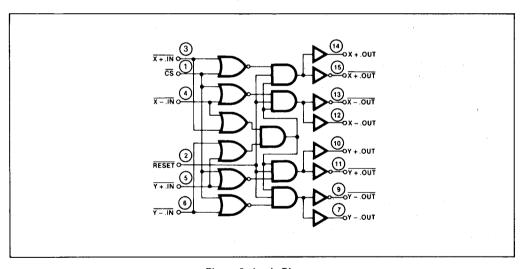


Figure 3. Logic Diagram



ABSOLUTE MAXIMUM RATINGS*

Ambient Temperature Under Bias40°C to +100°	С
Storage Temperature65°C to +150°	С
Voltage on Any Pin with	
Respect to Ground0.5 to V _{DD} +0.5	٧
Supply Voltage, Vpp0.5 to +14	٧
Output Current 250 m	Α
(One Output @ 100% Duty Cycle)	

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. CHARACTERISTICS (TA = see range specified on first page

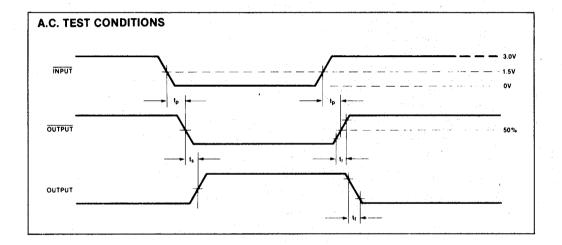
 $V_{DD} = 12V + 5\%$, -10%; unless otherwise specified)

Symbol Pa	Parameter	Limits				Total Conditions
	raiaineter	Min.	Тур.	Max.	Unit	Test Conditions
IIN	Input Current			5	μΑ	V _I = 0.8V
VIL	Low-Level Input Voltage			0.8	V	
VIH	High-Level Input Voltage	2.2			V	
V _{OL1}	Output Low Voltage			2.0	V	I _{OL} = 100 mA
V _{OL2}	Output Low Voltage			0.2	٧	I _{OL} = 10 mA
V _{OH1}	Output High Voltage	V _{DD} -2			V	I _{OH} = -100 mA
V _{OH2}	Output High Voltage	V _{DD} -0.2			٧	I _{OH} = -10 mA
loL	Output Sink Current	100			m A	V _{OL} = 2.0V
Іон	Output Source Current	100			m A	V _{OH} = V _{DD} -2.0V
I _{DD0}	Supply Current			4.5	mA	Chip Deselected: CS = V _{IH} V _{DD} = 12.6V
DD1	Supply Current			75	mA	f = 100 kHz, V _{DD} = 12.6V, Outputs Unloaded



A.C. CHARACTERISTICS (T_A = see range specified on first page $V_{DD} = 12V \pm 5\%$, unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
t _{p1}	Propagation Delay from X+.IN, XIN, Y+.IN, YIN			100	ns	500 pF Load
t _{p2}	Propagation Delay from CS or RESET			150	ns	500 pF Load
tr	Rise Time (10% to 90%)			45	ns	500 pF Load
tF	Fail Time (90% to 10%)		-	45	ns	500 pF Load
ts	Skew Between an Output and Its Complements			20	ns	



CAPACITANCE* $(T_A = 25^{\circ}C, V_{DD} = 0V, V_{BIAS} = 2V, f = 1 \text{ MHz})$

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
CIN	Input Capacitance			10	pF	

^{*}This parameter is periodically sampled and is not 100% tested.



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Printed in U.S.A./Q-90/11-82/15K/JR/JT